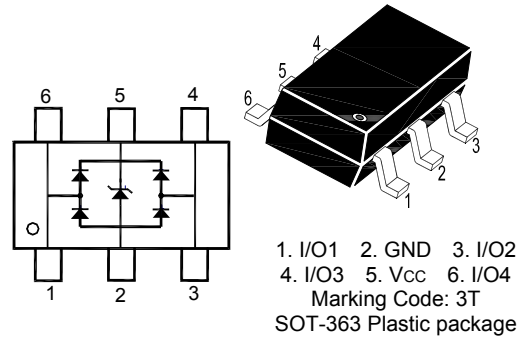


ESDLC0502DW

Low Capacitance TVS Array



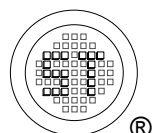
Absolute Maximum Ratings ($T_a = 25^\circ\text{C}$)

Parameter	Symbol	Value	Unit
Peak Pulse Current ($t_p = 8/20 \mu\text{s}$)	I_{PP}	3	A
Peak Pulse Power ($t_p = 8/20 \mu\text{s}$)	P_{PK}	50	W
ESD per IEC 61000-4-2 (Air) ¹⁾ ESD per IEC 61000-4-2 (Contact)	V_{ESD}	± 17 ± 14	KV
Operation Temperature Range	T_j	- 55 to + 125	$^\circ\text{C}$
Storage Temperature Range	T_{stg}	- 55 to + 150	$^\circ\text{C}$

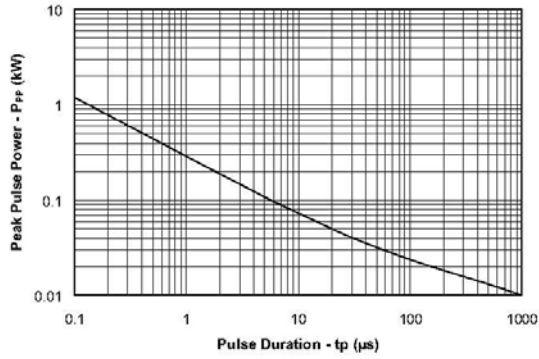
¹⁾ Between any I/O lines to GND

Characteristics at $T_a = 25^\circ\text{C}$

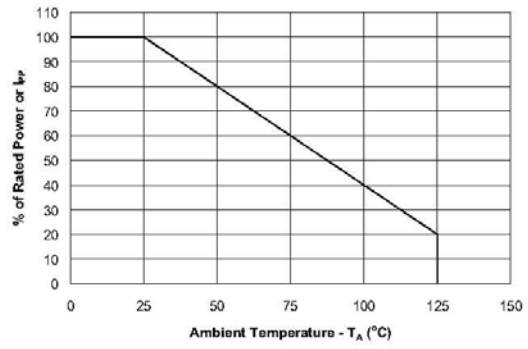
Parameter	Symbol	Min.	Max.	Unit
Reverse Stand-Off Voltage at Between I/O lines to Gnd or I/O to I/O	V_{RWM}	-	5	V
Reverse Breakdown Voltage at $I_t = 1 \text{ mA}$, Between I/O lines to GND	$V_{(BR)R}$	6	-	V
Reverse Current at $V_{RWM} = 5 \text{ V}$, at Between I/O lines to Gnd or I/O to I/O	I_R	-	3	μA
Clamping Voltage at $I_{PP} = 1 \text{ A}$, $t_p = 8/20 \mu\text{s}$, Between I/O lines to GND at $I_{PP} = 3 \text{ A}$, $t_p = 8/20 \mu\text{s}$, Between I/O lines to GND at $I_{PP} = 3 \text{ A}$, $t_p = 8/20 \mu\text{s}$, Between I/O to I/O	V_C	- - -	16 18 18	V
Junction Capacitance at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, Between I/O lines to GND at $V_R = 0 \text{ V}$, $f = 1 \text{ MHz}$, Between I/O to I/O	C_j	- -	0.9 0.7	pF



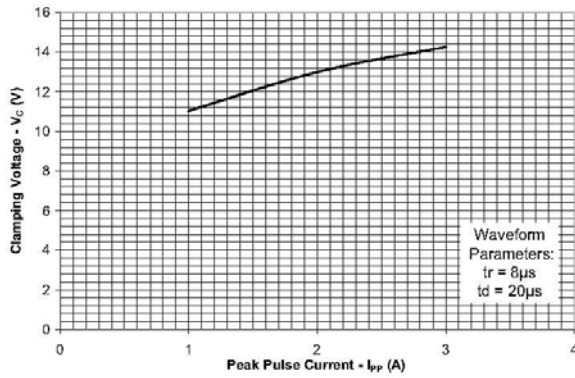
Non-Repetitive Peak Pulse Power vs. Pulse Time



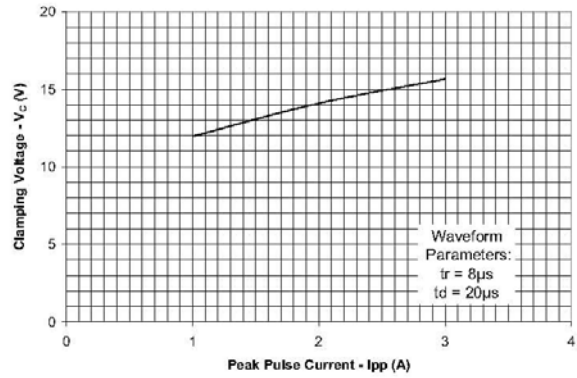
Power Derating Curve



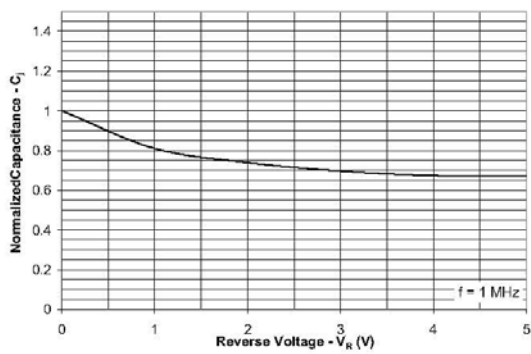
**Clamping Voltage vs. Peak Pulse Current
I/O to Gnd - Pin 1, 3, 4, 6 to Pin 2**



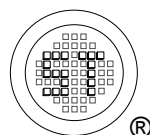
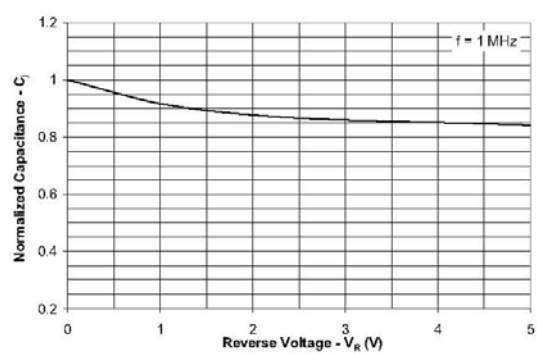
**Clamping Voltage vs. Peak Pulse Current
I/O to I/O**



**Normalized Capacitance vs. Reverse Voltage
I/O to Gnd - Pin 1, 3, 4, or 6 to Pin 2**

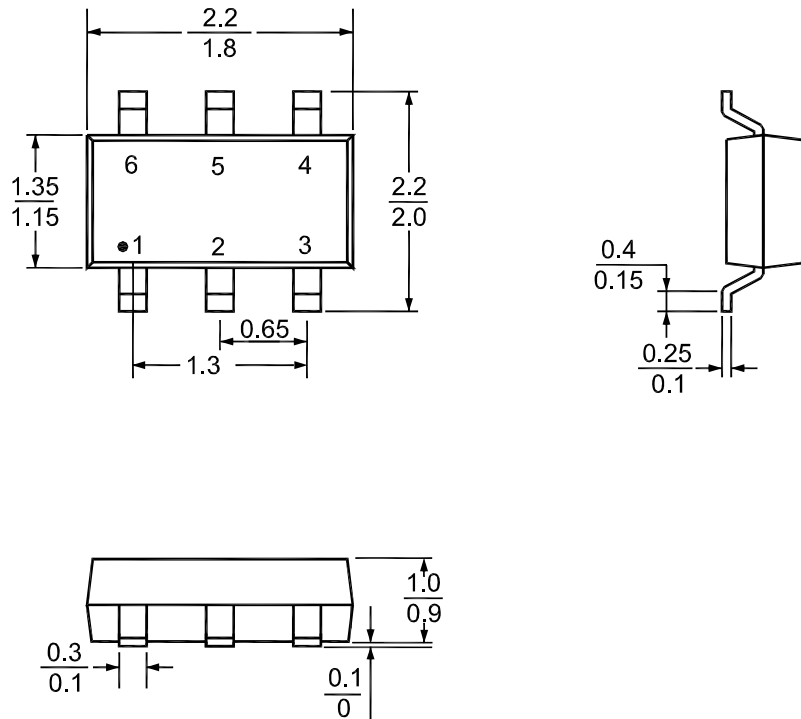


**Normalized Capacitance vs. Reverse Voltage
I/O to I/O**

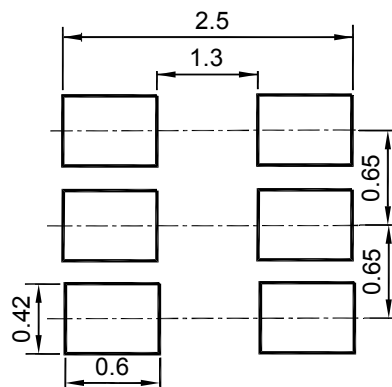


ESDLC0502DW

SOT-363 Package Outline Dimensions (Units: mm)



RECOMMENDED SOLDERING FOOTPRINT



SOT-363

